New Jersey Semi-Conductor Products, Inc.

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The 1N301, 1N301A and the 1N301B are hermetically sealed silicon junction diodes designed for general purpose applications and providing extreme stability, wide temperature range, high back resistance (100 meg-ohms or more), and high ratio of back to forward resistance. The flexible terminal leads may be soldered or welded directly to the terminals of circuit components without the use of sockets. Standard inline subminiature sockets may be used by cutting the leads to a suitable length.

MECHANICAL DATA

CASE: Metal and Glass BASE: None (0.016" tinned dumet wire, Length: 1.0" min. Spacing: 0.080" center-to-center)

TERMINAL CONNECTIONS : (Black dot is adjacent to Cathode Terminal)

ELECTRICAL DATA

RATINGS – ABSOLUTE MAXIMUM VALUES :

| | 114301 | INJUTA | 143010 | |
|---|---|--|--|--|
| Peak Inverse Voltage Average Rectified Current @25°C | 70 45 | 70 65 | 70 75 | Volts ma. |
| Average Rectified Current @ 100° C Average Rectified Current @ 150° C Surae Current (for 1 sec.) @ 25° C | 25 12 350 | 45 20 500 | 55 25 550 | mo. mo. |
| Surge Current (for 1 sec.) @ 100°C Ambient Temperature Range | 200 | 350 65 to + 150 | 350 | °C |
| Dissipation @25°C Derated above 25°C | 150 | 150 1 | 150 1 | mw∕⁰C mw∕°C |
| SPECIFIC CHARACTERISTICS : @25°C (Note 1) | | | | |
| Minimum Forward Current at +1 volt Maximum Reverse Current at —10 volts Maximum Reverse Current at —50 volts | 5 0.01 0.05 | 18 0.01 0.05 | 50 0.01 0.05 | mα. μα μα |
| TYPICAL CHARACTERISTICS : (Note 2) | | | | |
| Maximum Inverse Current at -10 volts (100° C) Maximum Inverse Current at -50 volts (100° C) Maximum Inverse Current at -10 volts (150° C) Maximum Inverse Current at -10 volts (150° C) Maximum Forward Current at $+1$ volt (100° C) Minimum Forward Current at $+1$ volt (100° C) Minimum Capacity at -10 volts (25° C) Maximum Capacity at -50 volts (25° C) Inverse Pulse Recovery (Note 3) 30 ma. x -35 volts and 10 ma. x -10 volts Recover to 5 K at 1 μ sec. 25 K at 2 μ sec. 80 K at 3 μ sec. 500 K at 5 μ sec. | 0.2 1.0 4.0 8.0 5 4 2 | 0-2 1.0 4.0 8.0 18 18 5 3 | 0.2 1.0 4.0 8.0 50 5.5 3 | μα μα μα ma, ma, μμtds μμtds |
| 5 ma. x -40 voits Recovers to 40 K at 1 µsec. 250 K at 2 µsec. 500 K at 3 µsec. 1 megohm at 5 µsec. | a a secondad | | | |
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SILICON JUNCTION DIODE

TYPE 1 N 3 O 1 1N301A 1 N 3 O 1 B





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